

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI VHB1-12T is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	400 mA (MAX)
V_{CB0}	40 V
V_{CEO}	20 V
V_{CER}	40 V
V_{EBO}	2.0 V
P_{DISS}	3.5 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	20 °C/W

PACKAGE STYLE TO-39

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.200 / 5.080	
B	.029 / 0.740	.045 / 1.140
C	.028 / 0.720	.034 / 0.860
D	.335 / 8.510	.370 / 9.370
E	.305 / 7.750	.335 / 8.500
F	.240 / 6.100	.260 / 6.600
G	.500 / 12.700	
H	.016 / 0.407	.020 / 0.508

ORDER CODE: ASI10711

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 5.0 mA	20			V
BV_{CER}	I _C = 5.0 mA R _{BE} = 10 Ω	40			V
BV_{EBO}	I _E = 100 μA	2.0			V
I_{CEO}	V _{CE} = 12 V			0.2	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	10		200	---
V_{CE(SAT)}	I _C = 100 mA I _B = 20 mA			0.5	Vdc
C_{OB}	V _{CB} = 12.5 V f = 1.0 MHz			4.0	pF
P_G η_C	V _{CE} = 12.5 V P _{OUT} = 1.0 W f = 175 MHz	10	60		dB %